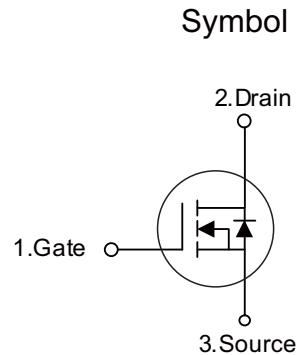


## ■ PRODUCT CHARACTERISTICS

VDSS	650V
R <sub>DS(on)</sub> Typ(@V <sub>GS</sub> =10 V)	2.4Ω
Qg@type	20nC
ID	4A



## ■ APPLICATIONS

- Electronic ballast
- Electronic transformer
- Switch mode power supply

## ■ FEATURES

- \* Low on-resistance
- \* High input resistance
- \* Rohs compliant

## ■ ORDER INFORMATION

Order codes		Package	Packing
Halogen-Free	Halogen		
N/A	MOT4N65F	TO-220F	50 pieces/Tube
N/A	MOT4N65A	TO-220	50 pieces/Tube

## ■ ABSOLUTE MAXIMUM RATINGS (T<sub>C</sub> = 25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	V <sub>DSS</sub>	650	V
Gate-Source Voltage	V <sub>GSS</sub>	±30	V
Avalanche Current (Note 2)	I <sub>AR</sub>	4.0	A
Drain Current	Continuous	I <sub>D</sub>	A
	Pulsed (Note 2)	I <sub>DM</sub>	A
Avalanche Energy	Single Pulsed (Note 3)	E <sub>AS</sub>	mJ
	Repetitive (Note 2)	E <sub>AR</sub>	mJ
Peak Diode Recovery dv/dt (Note 4)	dv/dt	4.5	V/ns
Power Dissipation	TO-220	106	W
	TO-22F	36	W
Junction Temperature	T <sub>J</sub>	+150	°C
Operating Temperature	T <sub>OPR</sub>	-55 ~ +150	°C
Storage Temperature	T <sub>STG</sub>	-55 ~ +150	°C

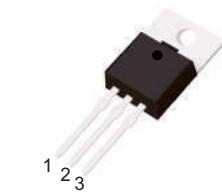
Note: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by maximum junction temperature

3. L = 30mH, I<sub>AS</sub> = 4A, V<sub>DD</sub> = 50V, R<sub>G</sub> = 25 Ω, Starting T<sub>J</sub> = 25°C

4. I<sub>SD</sub>≤4.4A, di/dt≤200A/μs, V<sub>DD</sub>≤BV<sub>DSS</sub>, Starting T<sub>J</sub> = 25°C



TO-220



TO-220F

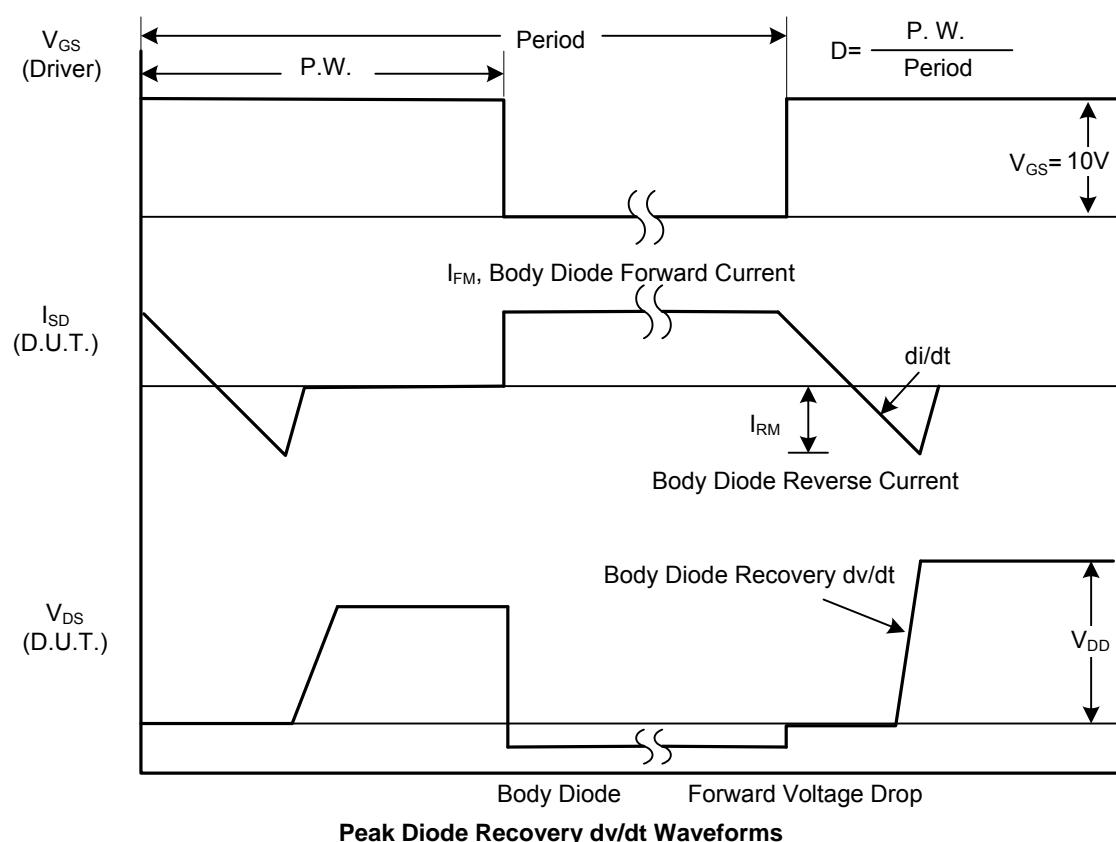
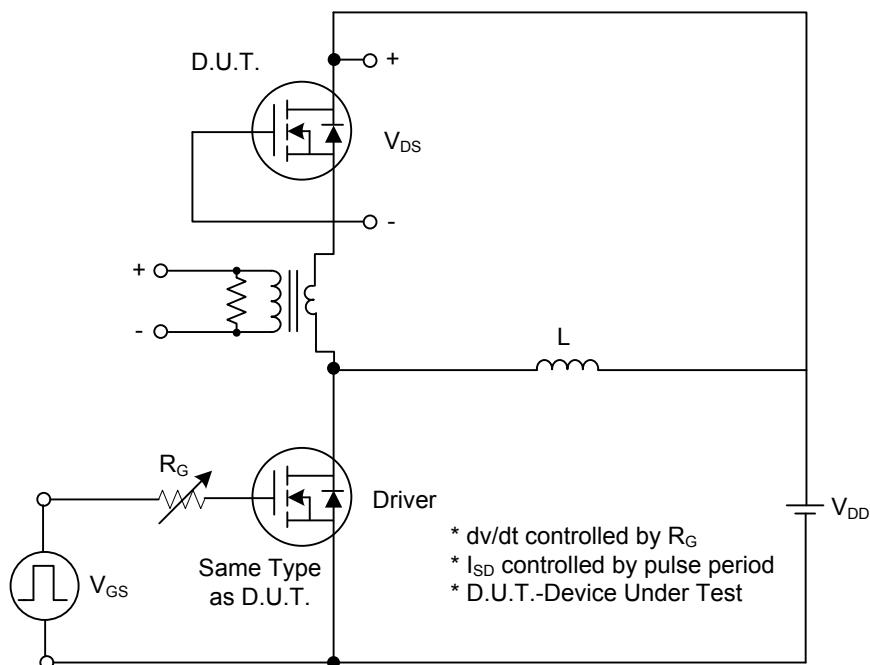
■ ELECTRICAL CHARACTERISTICS ( $T_C=25^\circ\text{C}$ , unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Drain-Source Breakdown Voltage	$\text{BV}_{\text{DSS}}$	$V_{\text{GS}} = 0 \text{ V}, I_{\text{D}} = 250 \mu\text{A}$	650	-	-	V
Drain-Source Leakage Current	$I_{\text{DSS}}$	$V_{\text{DS}} = 650 \text{ V}, V_{\text{GS}} = 0 \text{ V}$	-	-	10	$\mu\text{A}$
Gate-Source Leakage Current	Forward $I_{\text{GSS}}$	$V_{\text{GS}} = 30 \text{ V}, V_{\text{DS}} = 0 \text{ V}$	-	-	100	nA
	Reverse $I_{\text{GSS}}$	$V_{\text{GS}} = -30 \text{ V}, V_{\text{DS}} = 0 \text{ V}$	-	-	-100	nA
Breakdown Voltage Temperature Coefficient	$\Delta \text{BV}_{\text{DSS}}/\Delta T_J$	$I_{\text{D}} = 250 \mu\text{A}$ , Referenced to $25^\circ\text{C}$	-	0.6	-	$\text{V}/^\circ\text{C}$
On characteristics						
Gate Threshold Voltage	$V_{\text{GS(TH)}}$	$V_{\text{DS}} = V_{\text{GS}}, I_{\text{D}} = 250 \mu\text{A}$	2.0	-	4.0	V
Static Drain-Source On-State Resistance	$R_{\text{DS(ON)}}$	$V_{\text{GS}} = 10 \text{ V}, I_{\text{D}} = 2 \text{ A}$	-	2.4	2.8	$\Omega$
Dynamic characteristics						
Input Capacitance	$C_{\text{ISS}}$	$V_{\text{DS}} = 25 \text{ V}, V_{\text{GS}} = 0 \text{ V}, f = 1 \text{ MHz}$	-	520	-	pF
Output Capacitance	$C_{\text{OSS}}$		-	70	-	pF
Reverse Transfer Capacitance	$C_{\text{RSS}}$		-	8	-	pF
Switching characteristics						
Turn-On Delay Time	$t_{\text{D(ON)}}$	$V_{\text{DD}} = 325 \text{ V}, I_{\text{D}} = 4.0 \text{ A}, R_{\text{G}} = 25 \Omega$ (Note 1, 2)	-	13	-	ns
Turn-On Rise Time	$t_{\text{R}}$		-	45	-	ns
Turn-Off Delay Time	$t_{\text{D(OFF)}}$		-	25	-	ns
Turn-Off Fall Time	$t_{\text{F}}$		-	35	-	ns
Total Gate Charge	$Q_{\text{G}}$	$V_{\text{DS}} = 520 \text{ V}, I_{\text{D}} = 4 \text{ A}$ $V_{\text{GS}} = 10 \text{ V}$ (Note 1, 2)	-	15	-	nC
Gate-Source Charge	$Q_{\text{GS}}$		-	3.4	-	nC
Gate-Drain Charge	$Q_{\text{GD}}$		-	7.1	-	nC
Source-drain diode ratings and characteristics						
Drain-Source Diode Forward Voltage	$V_{\text{SD}}$	$V_{\text{GS}} = 0 \text{ V}, I_{\text{S}} = 4.0 \text{ A}$	-	-	1.4	V
Maximum Continuous Drain-Source Diode Forward Current	$I_{\text{S}}$		-	-	4.4	A
Maximum Pulsed Drain-Source Diode Forward Current	$I_{\text{SM}}$		-	-	17.6	A
Reverse Recovery Time	$t_{\text{rr}}$	$V_{\text{GS}} = 0 \text{ V}, I_{\text{S}} = 4.0 \text{ A}, dI_{\text{F}}/dt = 100 \text{ A}/\mu\text{s}$ (Note 1)	-	250	-	ns
Reverse Recovery Charge	$Q_{\text{RR}}$		-	1.5	-	$\mu\text{C}$

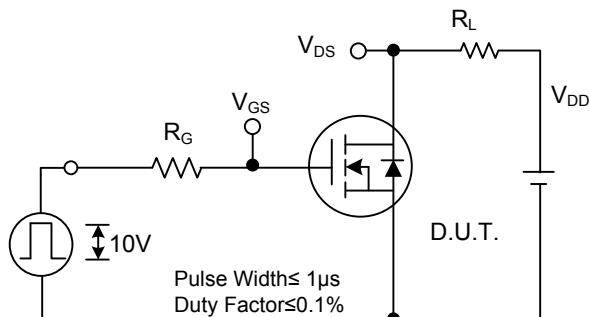
Note: 1. Pulse Test: Pulse width  $\leq 300 \mu\text{s}$ , Duty cycle  $\leq 2\%$

2. Essentially independent of operating temperature

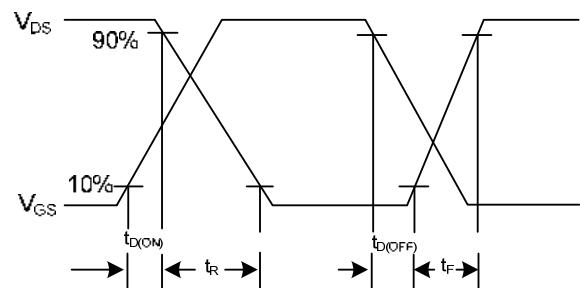
## ■ TEST CIRCUITS AND WAVEFORMS



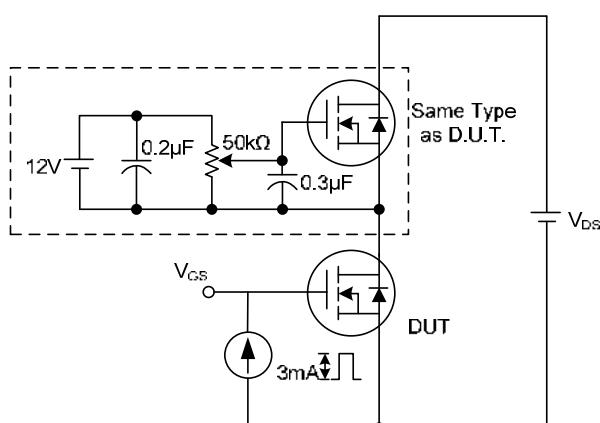
## ■ TEST CIRCUITS AND WAVEFORMS(Cont.)



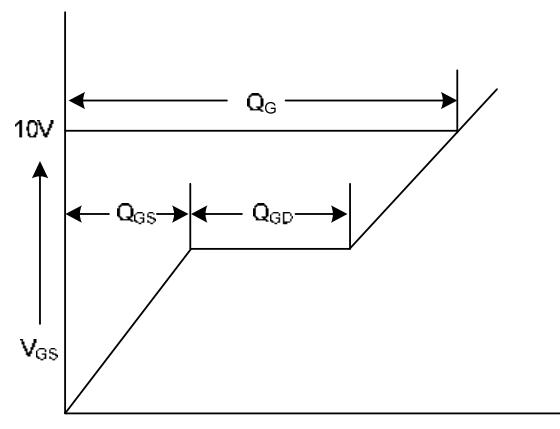
Switching Test Circuit



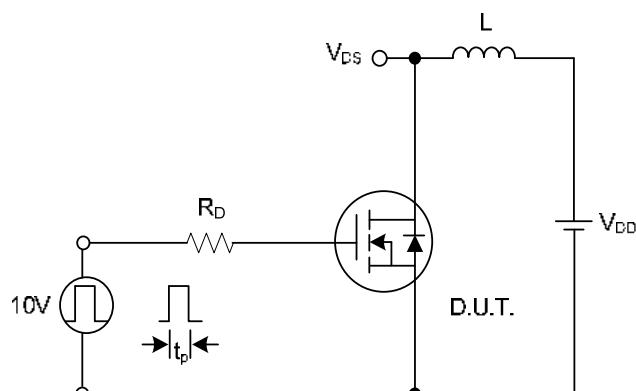
Switching Waveforms



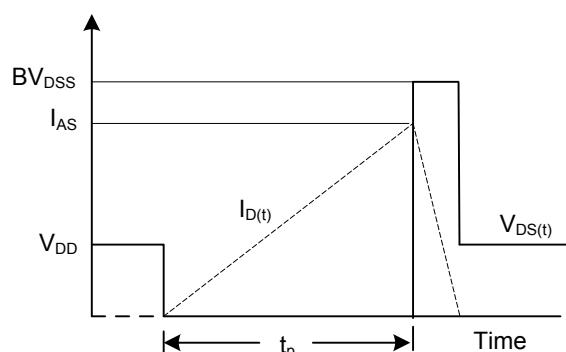
Gate Charge Test Circuit



Gate Charge Waveform

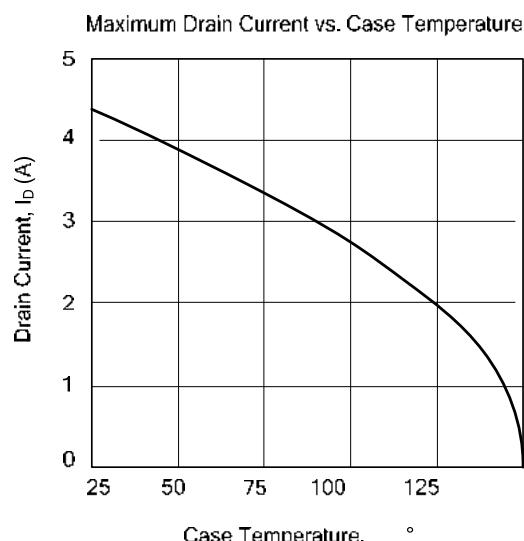
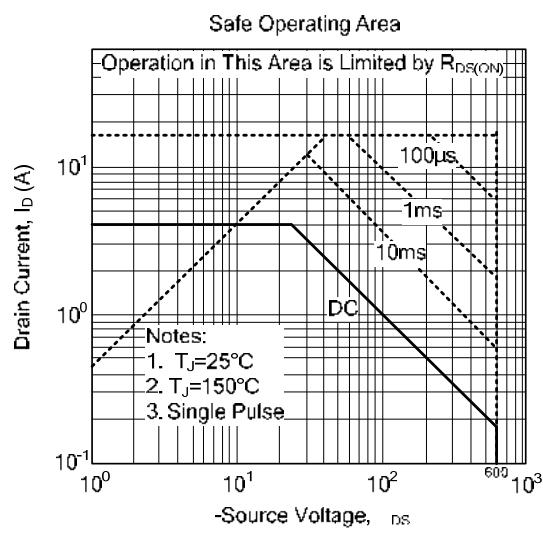
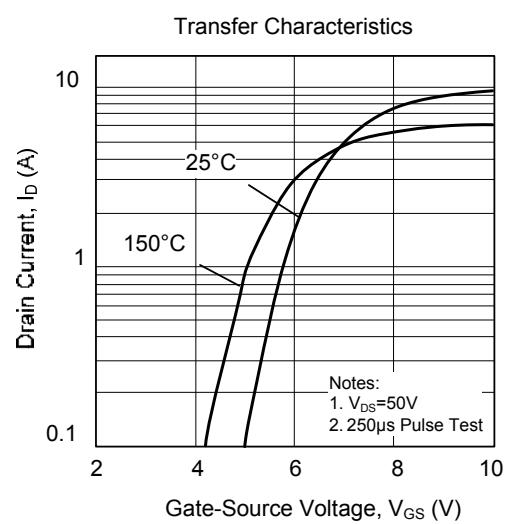
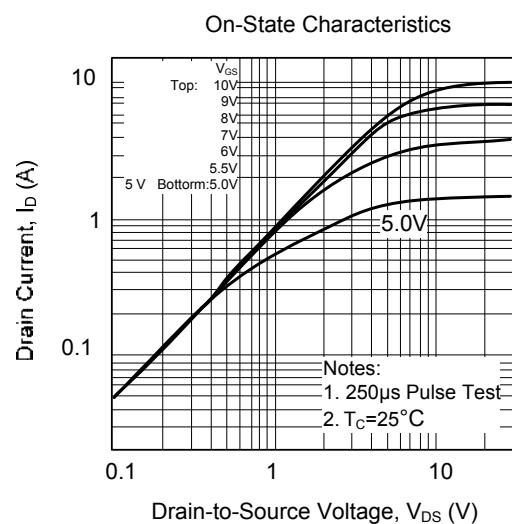
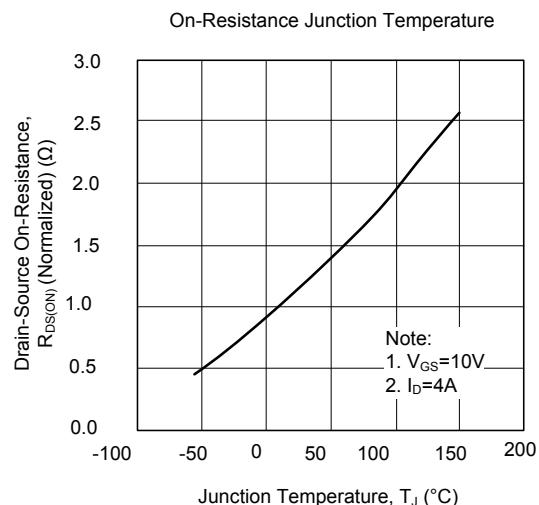
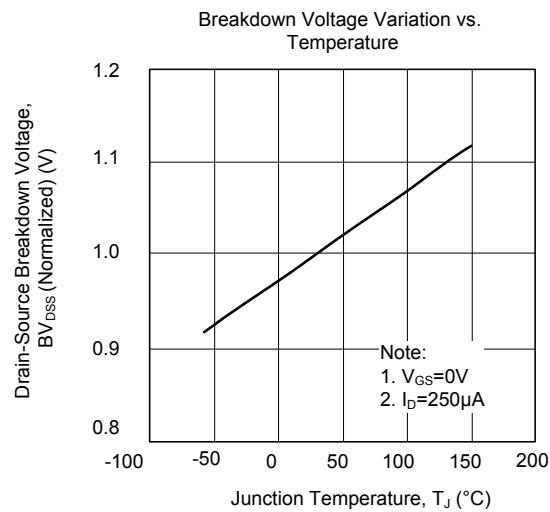


Unclamped Inductive Switching Test Circuit

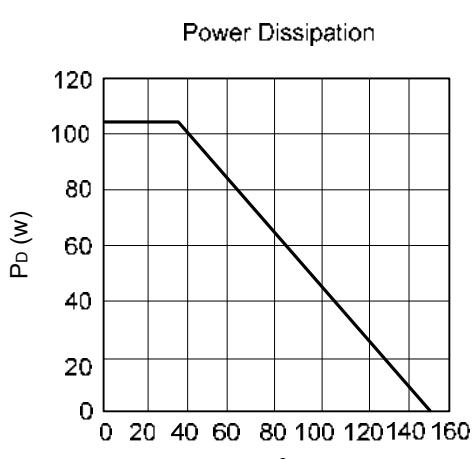
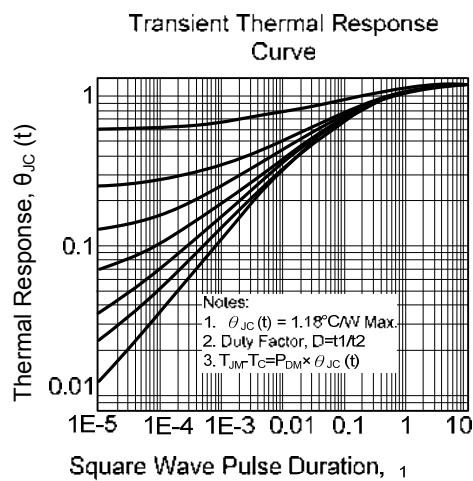
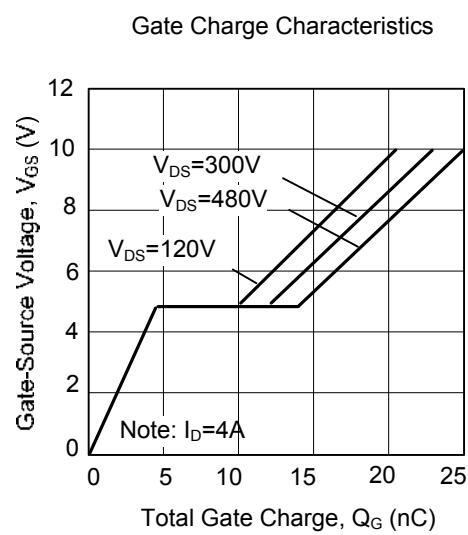
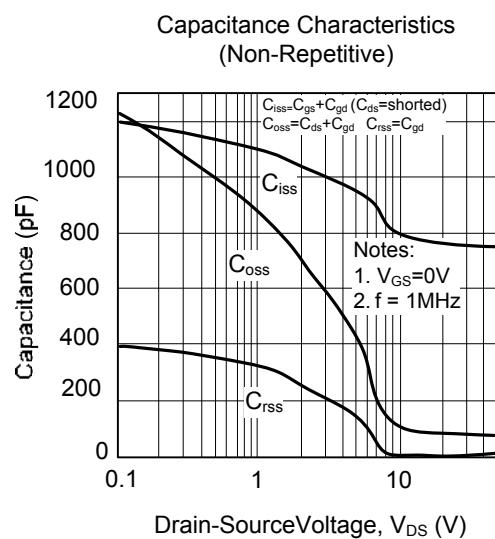
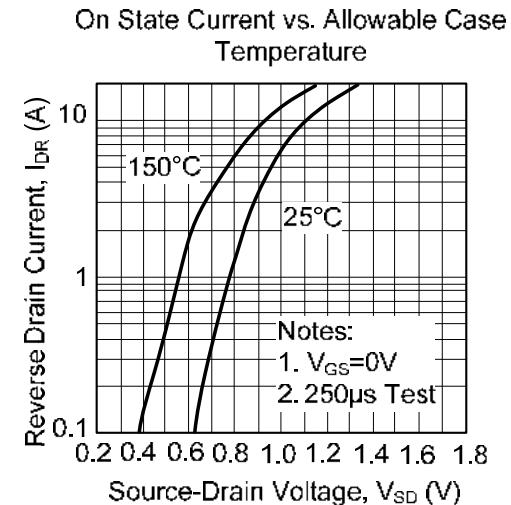
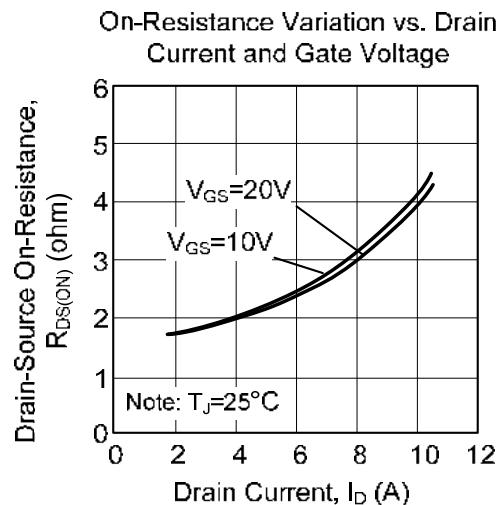


Unclamped Inductive Switching Waveforms

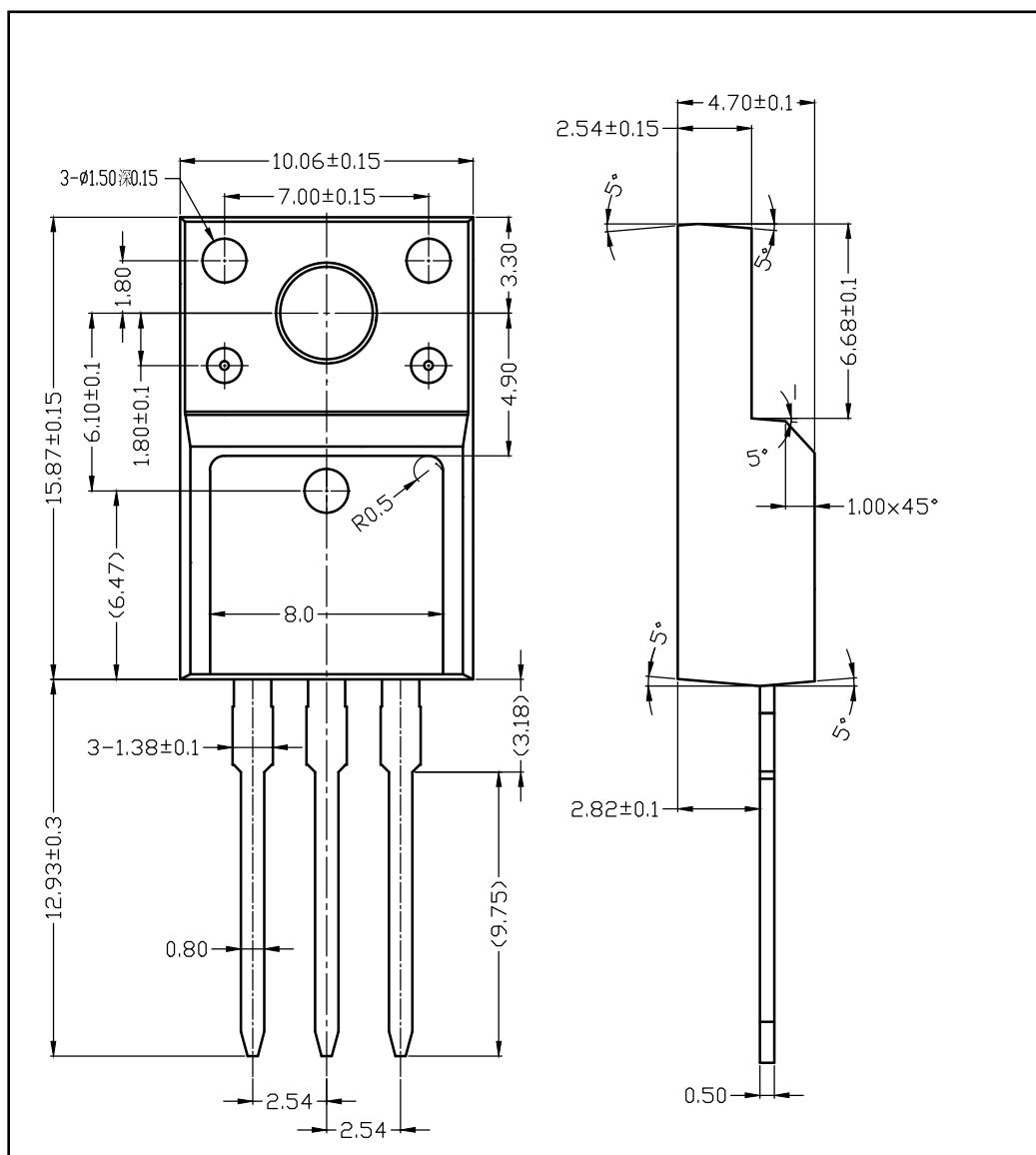
## ■ TYPICAL CHARACTERISTICS



## ■ TYPICAL CHARACTERISTICS(Cont.)



## ■ TO-220F-3L PACKAGE OUTLINE DIMENSIONS



## ■ TO-220-3L PACKAGE OUTLINE DIMENSIONS

